

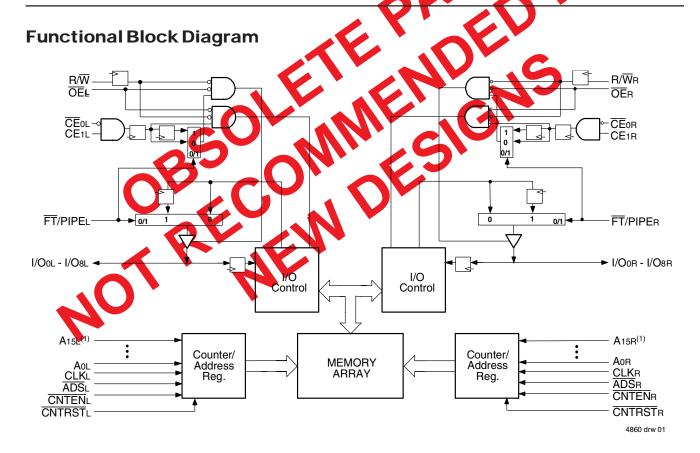
HIGH-SPEED 3.3V 64/32K x 9 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

IDT70V9189/79L OBSOLETE PART

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 6.5/7.5/9/12ns (max.)
 - Industrial: 9ns (max.)
- Low-power operation
 - IDT70V9189/79LActive: 500mW (typ.)Standby: 1.5mW (typ.)
- Flow-Through or Pipelined output mode on either port via the FT/PIPE pins
- Counter enable and reset features

- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
 - 4ns setup to clock and Ons hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 6.5ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 10ns cycle time, 100MHz operation in Pipeline output mode
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100-pin Thin Quad Flatpack (TQFP)



NOTE:

1. A₁₅x is a NC for IDT70V9179.

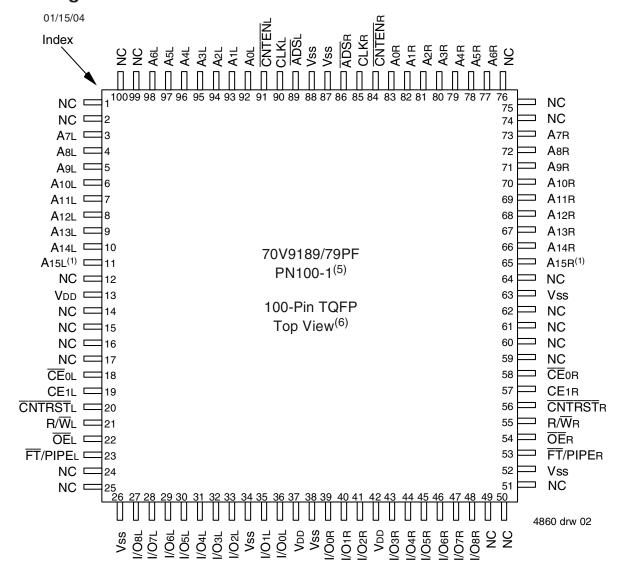
JANUARY 2009

Description:

The IDT70V9189/79 is a high-speed 64/32K x 9 bit synchronous Dual Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT70V9189/79 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}\text{O}$ and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 500mW of power.

Pin Configuration^(2,3,4)



- 1. A_{15x} is a NC for IDT70V9179.
- 2. All Vcc pins must be connected to power supply
- 3. All GND pins must be connected to ground.
- 4. Package body is approximately 14mm x 14mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

4860 tbl 02

Pin Names

Left Port	Right Port	Names			
CEOL, CE1L	CEOR, CE1R	Chip Enables			
$R/\overline{W}L$	R/W̄R	Read/Write Enable			
ŌĒL	OE R	Output Enable			
A0L - A15L ⁽¹⁾	A0R - A15R ⁽¹⁾	Address			
I/O0L - I/O8L	I/O0R - I/O8R	Data Input/Output			
CLKL	CLKR	Clock			
ADSL	ADS R	Address Strobe Enable			
CNTENL	<u>CNTEN</u> R	Counter Enable			
CNTRSTL	<u>CNTRST</u> R	Counter Reset			
FT/PIPEL	FT/PIPER	Flow-Through / Pipeline			
V	DD	Power (3.3V)			
V	SS	Ground (0V)			

NOTE:

- 1. Address A₁₅x is NC for IDT70V9179.
- 2. \overline{LB} and \overline{UB} are single buffered regardless of state of $\overline{FT}/PIPE$.
- 3. $\overline{\text{CE}}\text{o}$ and CE1 are single buffered when $\overline{\text{FT}}/\text{PIPE} = \text{VIL}$, CEo and CE1 are double buffered when FT/PIPE = VIH, i.e. the signals take two cycles to deselect.

4860 tbl 01

Truth Table I—Read/Write and Enable Control(1,2,3)

ŌĒ	CLK	Œ	CE1	R/ W	I/O ₀₋₈	MODE			
Х	↑	Н	Х	Χ	High-Z	Deselected-Power Down			
Х	↑	Χ	L	Χ	High-Z	Deselected-Power Down			
Х	↑	L	Н	L	DATAIN	Write			
L	↑	L	Н	Н	DATAout	Read			
Н	Х	L	Н	Χ	High-Z	Outputs Disabled			

NOTES:

- 1. "H" = V_{IH} , "L" = V_{IL} , "X" = Don't Care.
- 2. ADS, CNTEN, CNTRST = X.
- 3. $\overline{\mathsf{OE}}$ is an asynchronous input signal.

Truth Table II—Address Counter Control (1,2,3)

External Address	Previous Internal Address	Internal Address Used	CLK	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
An	Х	An	↑	L ⁽⁴⁾	Х	Н	Divo (n)	External Address Used
Х	An	An + 1	↑	Н	L ⁽⁵⁾	Н	Dvo(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	↑	Н	Н	Н	Dvo(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	A0	↑	Χ	Х	L ⁽⁴⁾	DI/O(0)	Counter Reset to Address 0

4860 tbl 03 NOTES:

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. $\overline{\text{CE}}_0$ and $\overline{\text{OE}}$ = VIL; CE1 and R/ $\overline{\text{W}}$ = VIH.
- 3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.
 4. ADS and CNTRST are independent of all other signals including CEo and CE1.
- 5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CEo and CE1.

Recommended Operating Temperature and Supply Voltage

Grade	Ambient Temperature ⁽²⁾	GND	V _{DD}
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

NOTES

1. This is the parameter Ta. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	V
VIH	Input High Voltage	2.0V	_	Vcc+0.3V ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	V

4860 tbl 05

NOTES

4860 tbl 04

- 1. $V_{IL} \ge -1.5V$ for pulse width less than 10 ns.
- 2. VTERM must not exceed VDD +0.3V.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
TJN	Junction Temperature	+150	°C
Іоит	DC Output Current	50	mA

4860 tbl 06

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed VDD +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDD + 0.3V.
- ${\it 3.} \quad {\it Ambient Temperature Under DC Bias.} \ {\it NO AC Conditions.} \ {\it Chip Deselected.}$

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, f = 1.0MHz)$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

NOTES

- These parameters are determined by device characterization, but are not production tested.
- 2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references Ci/o.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 0.3V)

			70V9189/79L		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	$V_{DD} = 3.6V$, $V_{IN} = 0V$ to V_{DD}	_	5	μΑ
ILO	Output Leakage Current	$\overline{\text{CE}}$ = ViH or CE1 = ViL, VouT = 0V to VDD	_	5	μΑ
Vol	Output Low Voltage	IoL = +4mA	_	0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4	_	V

NOTE:

1. At $VDD \le 2.0V$ input leakages are undefined.

4860 tbl 08

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽³⁾ (V_{DD} = 3.3V ± 0.3V)

						39/79L6 I Only		89/79L7 I Only		39/79L9 & Ind		9/79L12 Only	
Symbol	Parameter	Test Condition	Versio	n	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
Icc	Dynamic Operating Current (Both	CEL and CER= VIL,	COM'L	L	220	350	200	310	180	260	150	230	mA
	Ports Active)	Outputs Disabled, $f = fMAX^{(1)}$	IND	L	_	_	_	_	180	280		_	
ISB1	Standby Current (Both Ports - TTL	CEL = CER = VIH	COM'L	L	70	130	65	130	50	100	40	80	mA
	Level Inputs)	$f = fMAX^{(1)}$	IND	L		_	_	_	50	120	-	_	
ISB2	Standby Current (One	$\overline{\underline{CE}}$ "A" = VIL and $\overline{\overline{CE}}$ "B" = VIH ⁽⁵⁾	COM'L	L	150	250	140	245	110	190	100	175	mA
	Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L	1	_	—		110	205		1	
ISB3	Full Standby Current (Both	Both Ports CEL and CER > VDD - 0.2V,	COM'L	L	0.4	3	0.4	3	0.4	3	0.4	3	mA
	Ports - CMOS Level Inputs)	$VIN \ge VDD - 0.2V \text{ or } VIN \le 0.2V, f = 0^{(2)}$	IND	L					0.4	6	_	_	
ISB4	Full Standby Current (One Port - CMOS	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VDD - 0.2V$ ⁽⁵⁾	COM'L	L	140	240	130	235	100	180	90	165	mA
	Level Inputs)	$ \begin{array}{l} \text{VIN} \geq \text{VDD} - 0.2 \text{V or} \\ \text{VIN} \leq 0.2 \text{V, Active Port,} \\ \text{Outputs Disabled, f = fMAX}^{(1)} \\ \end{array} $	IND	L	_	_	_	_	100	195	_	_	

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, $TA = 25^{\circ}C$ for Typ, and are not production tested. $Icc \ DC(f=0) = 90mA$ (Typ).
- 5. \overline{CEx} = VIL means \overline{CEox} = VIL and CE1x = VIH \overline{CEx} = VIH means \overline{CEox} = VIH or CE1x = VIL

 - $\begin{array}{c} \overline{\text{CE}} x \leq 0.2 \text{V means } \overline{\text{CE}} 0x \leq 0.2 \text{V and } \text{CE} 1x \geq \text{Vcc 0.2V} \\ \overline{\text{CE}} x \geq \text{Vdd 0.2V means } \overline{\text{CE}} 0x \geq \text{Vdd 0.2V or CE} 1x \leq 0.2 \text{V} \\ \end{array}$
 - "X" represents "L" for left port or "R" for right port.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

4860 tbl 10

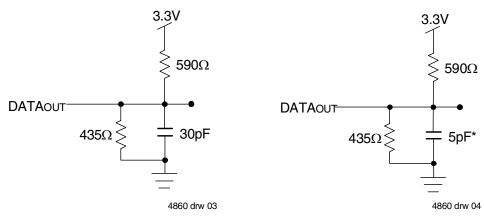


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz).
*Including scope and jig.

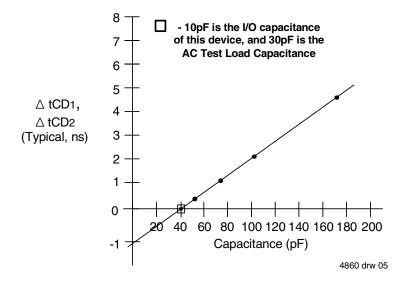


Figure 3. Typical Output Derating (Lumped Capacitive Load).

4860 tbl 11

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3)}$ (VDD = 3.3V ± 0.3V, TA = 0°C to +70°C)

	(VIII)		89/79L6 I Only	70V9189/79L7 Com'l Only		70V9189/79L9 Com'l & Ind		70V9189/79L12 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	19		22	_	25	_	30		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	10	_	12	_	15	_	20		ns
tcH1	Clock High Time (Flow-Through) ⁽²⁾	6.5		7.5	_	12	_	12		ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	6.5		7.5	_	12	_	12		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	4		5	_	6	_	8		ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	4		5	_	6	_	8		ns
tr	Clock Rise Time		3		3		3		3	ns
tF	Clock Fall Time		3		3		3		3	ns
tsa	Address Setup Time	3.5		4	_	4	_	4		ns
tha	Address Hold Time	0		0	_	1	_	1		ns
tsc	Chip Enable Setup Time	3.5		4	_	4	_	4		ns
thc	Chip Enable Hold Time	0	_	0	_	1	_	1		ns
tsw	R/W Setup Time	3.5	_	4	_	4	_	4		ns
thw	R/W Hold Time	0	_	0	_	1	_	1		ns
tsd	Input Data Setup Time	3.5	_	4	_	4	_	4		ns
tho	Input Data Hold Time	0	_	0	_	1	_	1		ns
tsad	ADS Setup Time	3.5	_	4	_	4	_	4		ns
thad	ADS Hold Time	0	_	0	_	1	_	1		ns
tscn	CNTEN Setup Time	3.5	_	4	_	4	_	4		ns
thcn	CNTEN Hold Time	0		0	_	1	_	1		ns
tsrst	CNTRST Setup Time	3.5		4	_	4	_	4		ns
thrst	CNTRST Hold Time	0	_	0	_	1	_	1		ns
toe	Output Enable to Data Valid		6.5		9		12	_	12	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2		2	_	2	_	2		ns
tohz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	1	7	ns
tcD1	Clock to Data Valid (Flow-Through) ⁽²⁾		15		18		20		25	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		6.5		7.5	_	9	_	12	ns
tDC	Data Output Hold After Clock High	2		2	_	2	_	2		ns
tckhz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2	_	2		2		2		ns
Port-to-Port [Delay									
tcwdd	Write Port Clock High to Read Data Delay		24		28		35	_	40	ns
tccs	Clock-to-Clock Setup Time		9		10	_	15	_	15	ns

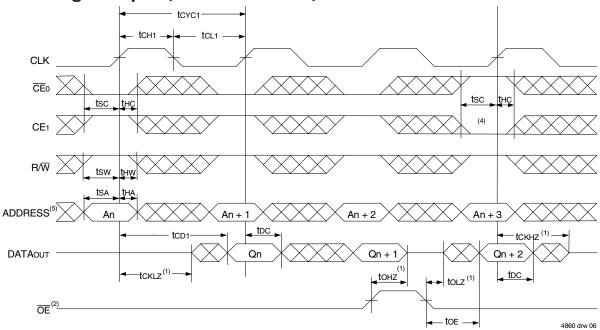
NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

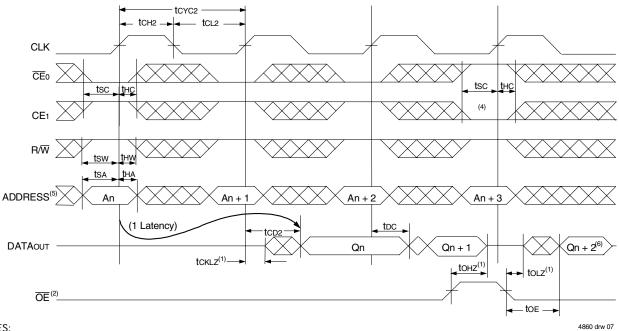
^{2.} The Pipelined output parameters (tcyc2, tcb2) apply to either or both the Left and Right ports when FT/PIPE = VIH. Flow-through parameters (tcyc1, tcb1) apply when FT/PIPE = VIL for that port.

^{3.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER, and FT/PIPEL.

Timing Waveform of Read Cycle for Flow-Through Output (FT/PIPE"x" = VIL)(3,6)

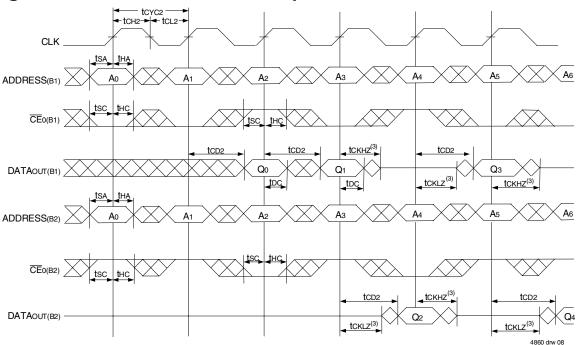


Timing Waveform of Read Cycle for Pipelined Output $(\overline{FT}/PIPE"x" = VIH)^{(3,6)}$

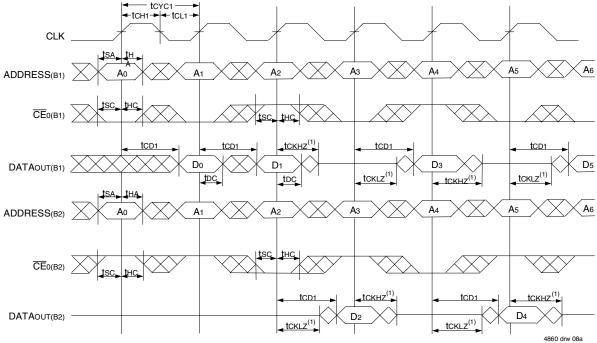


- NOTES:
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{CNTRST} = VIH$.
- 4. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0 = \text{V}_{\text{IH}}$ or $\text{CE}_1 = \text{V}_{\text{IL}}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 6. "X' here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)



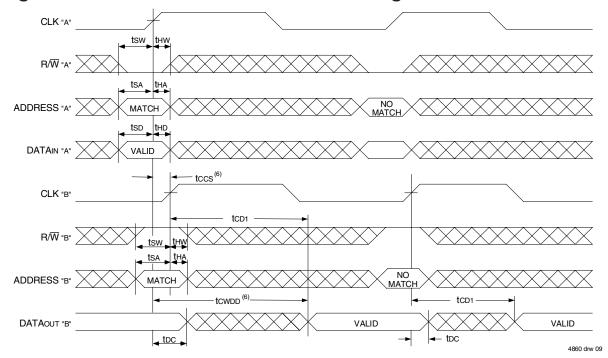
Timing Waveform of a Bank Select Flow-Through Read⁽⁶⁾



- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9089/79 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{OE}}$ and $\overline{\text{ADS}}$ = ViL; CE1(B1), CE1(B2), R/W, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = ViH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}} = \text{ViL}$; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}} = \text{ViH}$.
- 5. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpb.

 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.

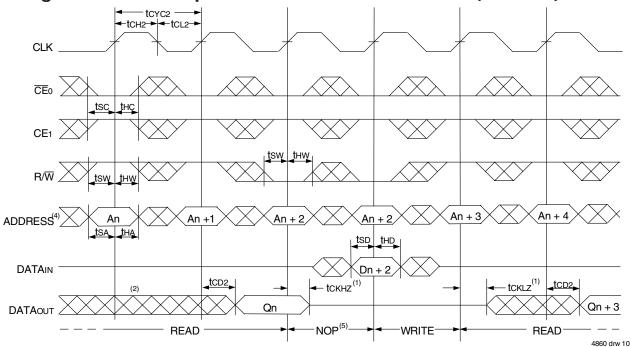
Timing Waveform with Port-to-Port Flow-Through Read^(4,5,7)



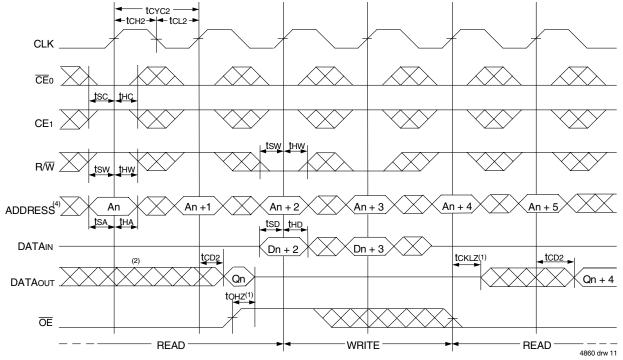
- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9189/79 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{OE}}$, and $\overline{\text{ADS}} = \text{VIL}$; CE1(B1), CE1(B2), R/ $\overline{\text{W}}$, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}} = \text{VIH}$.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}} = \text{Vil.}$; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}} = \text{ViH.}$
- 5. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpb.

 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read (OE = VIL)(3)

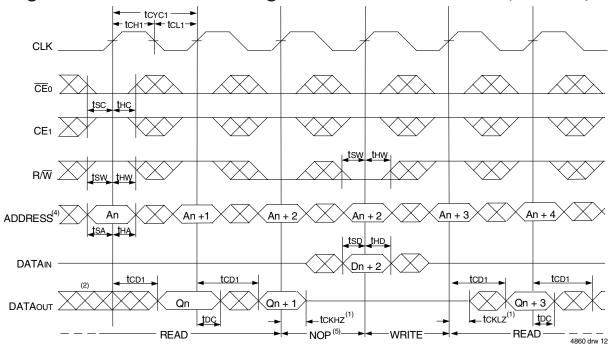


Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(3)

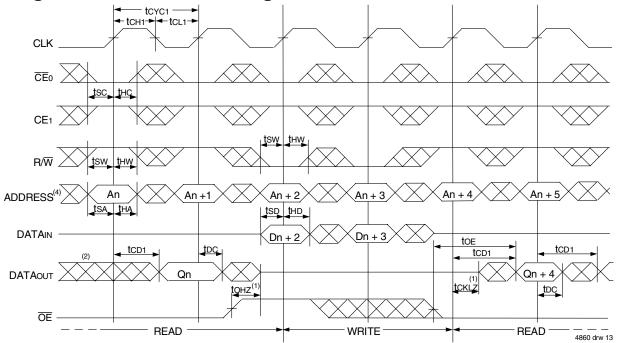


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}} = \text{Vil.}$; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}} = \text{Vih.}$ "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** = VIL)⁽³⁾

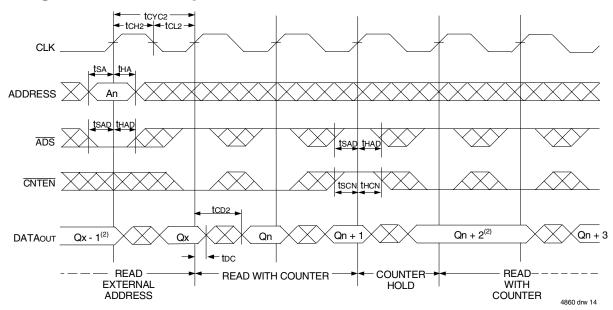


Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

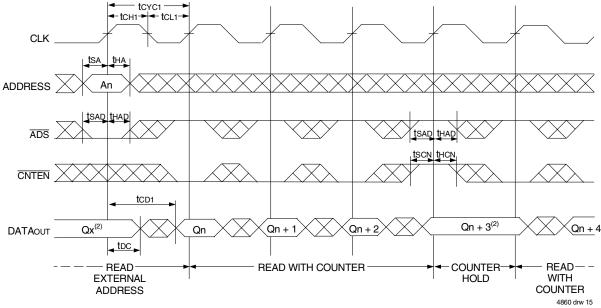


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}} = \text{VIL}$; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}} = \text{VIH}$. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since \overline{ADS} = V_{IL} constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

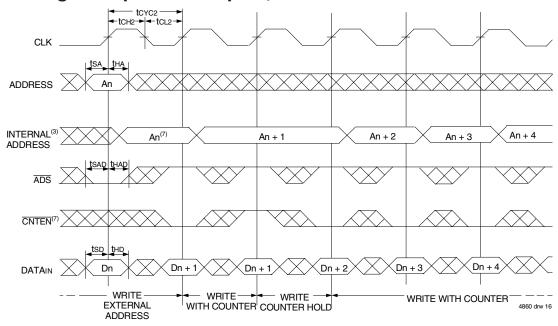


Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾

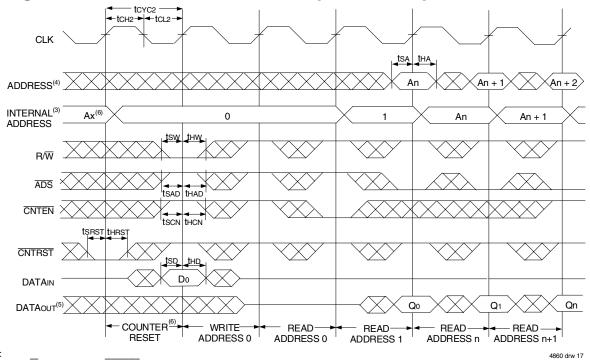


- 1. \overline{CE}_0 and \overline{OE} = V_{IL}; CE₁, R/ \overline{W} , and \overline{CNTRST} = V_{IH}.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)(1)



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



NOTES: 1. $\overline{\text{CE}}_0$ and $\overline{\text{R/W}} = \text{Vil}$; CE1 and $\overline{\text{CNTRST}} = \text{ViH}$.

- 2. $\overline{CE}_0 = VIL$; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.

Functional Description

The IDT70V9189/79 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

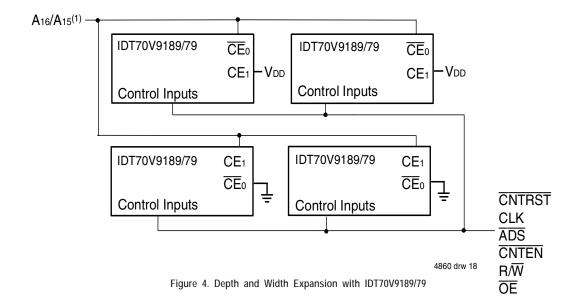
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to staff the operation of the address counters for fast interleaved memory applications.

 $\overline{\text{CE}}_0$ = VIH or CE1 = VIL for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9189/79's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0$ = VIL and CE1 = VIH to re-activate the outputs.

Depth and Width Expansion

The IDT70V9189/79 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

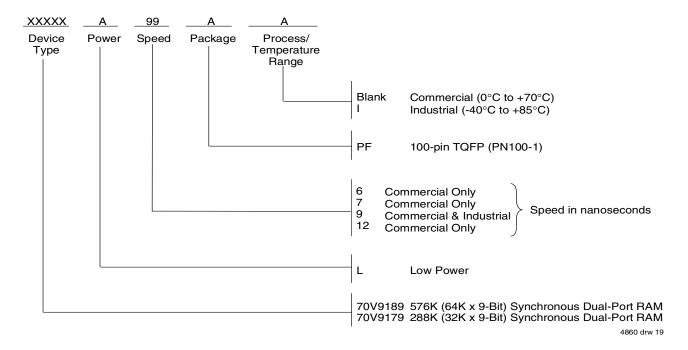
The IDT70V9189/79 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 18-bit or wider applications.



NOTE:

1. A₁₆ is for IDT70V9189. A₁₅ is for IDT70V9179.

Ordering Information



IDT Clock Solution for IDT70V9189/79 Dual-Port

				- 1				
	Dual-Port I/O Specifications Clock Specifications				Dual-Port I/O Specifications Clock Specifications			IDT
IDT Dual-Port Part Number	Voltage	I/O	Cycle		Maximum Frequency	Jitter Tolerance	IDT PLL Clock Device	Non-PLL Clock Device
70V9189/79	3.3	LVTTL	9pF	40%	100	150ps	2305 2308 2309	49FCT3805 49FCT3805D/E 74FCT3807 74FCT3807D/E

4860 tbl 12

Datasheet Document History

9/30/99: Initial Public Release 11/12/99: Replaced IDT logo

1/10/01: Page 3 Changed information in Truth Table II

Page 4 Increased storage temperature parameters

Clarified TA parameter

Page 5 DC Electrical parameters-changed wording from "open" to "disabled"

Changed ±200mV to 0mV in notes

Removed Preliminary status

01/15/04: Consolidated multiple devices into one datasheet

Changed naming conventions from Vcc to Vdd and from GND to Vss

Removed I-temp footnote

Page 2 Added date revision to pin configuration

Page 4 Added Junction Temperature to Absolute Maximum Ratings Table

Added Ambient Temperature footnote

Page 5 Added I-temp numbers for 9ns speed to the DC Electrical Characteristics Table

Added 6ns speed DC power numbers to the DC Electrical Characteristics Table

Page 7 Added I-temp for 9ns speed to AC Electrical Characteristics Table

Added 6ns speed AC timing numbers to the AC Electrical Characteristics Table

Page 15 Added 6ns speed grade and 9ns I-temp to ordering information

Added IDT Clock Solution Table

01/29/09: Page 16 Removed "IDT" from orderable part number 04/26/09: PDN-F-09-01 issued. See IDT.com for PDN specifics 12/05/13: 70V9189 Datasheet changed to Obsolete Status

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